

HSU83

Silicon Epitaxial Planar Diode for High Voltage Switching

HITACHI

ADE-208-307A(Z)

Rev 1

June 1996

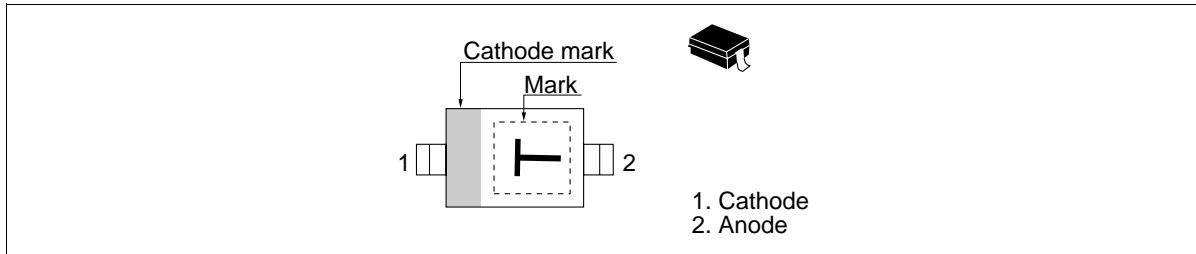
Features

- High reverse voltage. ($V_R=250V$)
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU83	T	URP

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	VRM	300	V
Reverse voltage	VR	250	V
Peak forward current	IFM	300	mA
Non-Repetitive peak forward surge current	IFSM*1	2	A
Average rectified current	IO	100	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55~+125	°C

Note 1. Value at duration of 10msec.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	VF	~	~	1.2	V	IF = 100 mA
Reverse current	IR1	~	~	0.2	μA	VR = 250V
	IR2	~	~	100		VR = 300V
Capacitance	C	~	~	3.0	pF	VR = 0V, f = 1 MHz
Reverse recovery time	trr	~	~	100	ns	IF = IR = 30 mA, Irr = 3mA

Main Characteristic

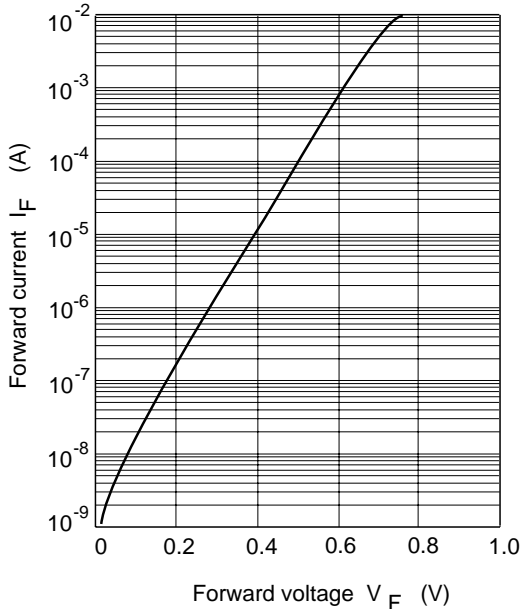


Fig.1 Forward current Vs. Forward voltage

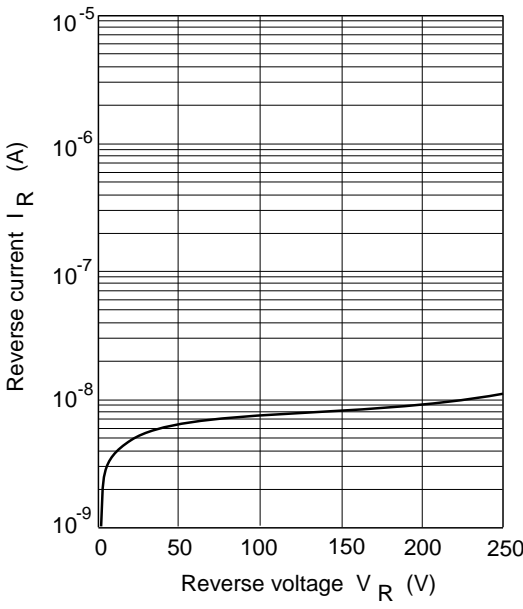


Fig.2 Reverse current Vs. Reverse voltage

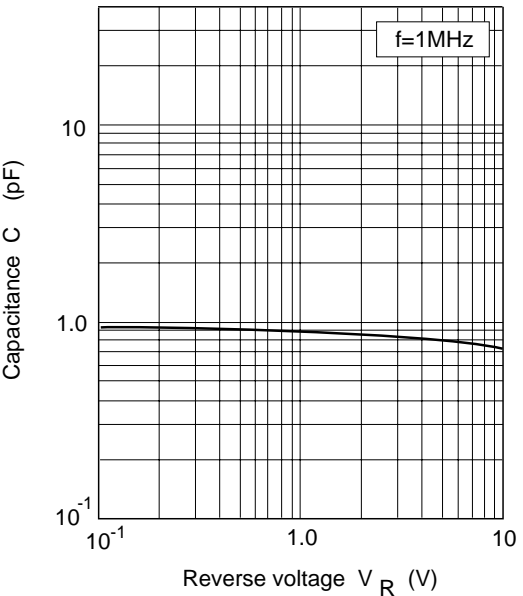


Fig.3 Capacitance Vs. Reverse voltage

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Package Dimensions

Unit : mm

